2 66	L Number	Hits	Search Text	DB	Time stamp
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3 0 5659191.pn. and (gate adj length)			, ,	1	
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2 0 5659191.pn. and (gate adj width)					
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8 11 (peripheral adj portion) and (gate adj	'	1	5659191.pn. and (length or width)	1	2003/05/17 09:51
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9 203 oxidized adj insulating adj (film or layer or region) 10 95 (oxidized adj insulating adj (film or layer or region)) 10 95 (oxidized adj insulating adj (film or layer or region)) and (257/\$.ccls. or layer or region) and (257/\$.ccls. or layer or region)) and (257/\$.ccls. or layer or region))) and (257/\$.ccls. or layer or layer or layer or layer or layer or layer or region))) and (257/\$.ccls. or layer or layer or layer or layer or region))) and (257/\$.ccls. or layer or layer or layer or layer or region))) and (257/\$.ccls. or layer la	~	11			2000,00,1, 11.04
9 203 oxidized adj insulating adj (film or layer or region) 10 95 (oxidized adj insulating adj (film or layer or region)) and (257/\$.ccls. or layer or layer or region)) and (257/\$.ccls. or layer or layer or layer or region)) and (257/\$.ccls. or layer or					
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10					
10 95 (oxidized adj insulating adj (film or layer or region)) and (257/\$.ccls. or 950; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB U					
layer or region)) and (257/\$.ccls. or 438/4.ccls.) (oxidized adj insulating adj (film or layer or region)) and (257/\$.ccls. or 438/4.ccls.) and (nonvolatile adj memory) ((prevent adj (oxidizing or oxidation)) same (insulating adj (film or layer or region))) and (257/\$.ccls. or 438/4.ccls.) ((prevent adj (oxidizing or oxidation)) same (insulating adj (film or layer or region))) and (257/\$.ccls. or 438/4.ccls.) 2 5479054.pn. and (prevent) 14 0 5479054.pn. and (oxidized) 15 1 5479054.pn. and (oxidation) 16 2 5479054.pn. and (oxidation) 17 2 5479054.pn. and (oxidation) 18 2 5479054.pn. and (oxidation) 19 2003/05/17 10:18 10 5479054.pn. and (oxidation) 10 5479054.pn. and (oxidation) 11 5479054.pn. and (oxidation)	10	0.5	(outdined odd inoulation odd (film or		2002/05/17 00:00
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11 3 (oxidized adj insulating adj (film or layer or region)) and (257/\$.ccls. or 438/4.ccls.) and (nonvolatile adj memory) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT;		•			
11 3 (oxidized adj insulating adj (film or layer or region)) and (257/\$.ccls. or 438/4.ccls.) and (nonvolatile adj memory) (prevent adj (oxidizing or oxidation)) Same (insulating adj (film or layer or region))) and (257/\$.ccls. or 438/4.ccls.) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; E			130/1.0013./		
11 3 (oxidized adj insulating adj (film or layer or region)) and (257/\$.ccls. or 438/4.ccls.) and (nonvolatile adj memory) USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; ISM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	1 V				
layer or region)) and (257/\$.ccls. or 438/4.ccls.) and (nonvolatile adj memory) 12	11	3	(oxidized adj insulating adj (film or		2003/05/17 09:09
138		-			
159 ((prevent adj (oxidizing or oxidation)) Same (insulating adj (film or layer or region))) and (257/\$.ccls. or 438/4.ccls.) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
159 ((prevent adj (oxidizing or oxidation)) same (insulating adj (film or layer or region))) and (257/\$.ccls. or 438/4.ccls.) 13			•	1	
Same (insulating adj (film or layer or region))) and (257/\$.ccls. or 438/4.ccls.) US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;					
region))) and (257/\$.ccls. or 438/4.ccls.) EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	12	159		1	2003/05/17 09:27
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;		ļ			
13 2 5479054.pn. and (prevent) IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; U		İ	region))) and (257/\$.ccls. or 438/4.ccls.)		
13 2 5479054.pn. and (prevent) USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;				·	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	13	ا ۾	5470054 pp and /provent)		2003/05/17 10:20
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	13	2	54/9054.pn. and (prevent)		2003/05/1/ 10:38
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;		ĺ		1	
14 0 5479054.pn. and (oxidized)	9-7-80			1	
14 0 5479054.pn. and (oxidized) USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;		Ī			
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EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT;		-			
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;					
1 5479054.pn. and (oxidation) USPĀT; US-PGPUB; EPO; JPO; DERWENT;					
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EPO; JPO; DERWENT;	15	1	5479054.pn. and (oxidation)	i i	2003/05/17 10:03
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16	0	5479054.pn. and (nonvolatile)	USPAT;	2003/05/17 10:18
10		3475054.pii. and (nonvoidelle)	US-PGPUB;	2003/03/1/ 10.10
			EPO; JPO;	
			DERWENT;	
ŀ			IBM_TDB	
17	0	5479054.pn. and (non adj volatile)	USPAT;	2003/05/17 10:18
	ĺ		US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
18	0	5479054.pn. and (memory)	USPAT;	2003/05/17 10:19
10	· •	dia (memory)	US-PGPUB;	2003/03/1/ 10:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
19	0	5479054.pn. and dram	USPAT;	2003/05/17 10:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
20	0	5479054.pn. and sram	IBM_TDB USPAT;	2003/05/17 10:19
20		J479034.pii. and Stam	US-PGPUB;	2003/03/17 10:19
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
21	0	5479054.pn. and ram	USPAT;	2003/05/17 10:20
		-	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
22	0	5479054.pn. and prom	USPAT;	2003/05/17 10:54
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
23	1	5747370.pn. and (oxidized or oxidation)	USPAT;	2003/05/17 10:53
	_	ovivorotpin ana (onizazioa oi onizazion)	US-PGPUB;	2000,00,11 20100
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
24	0	5747370.pn. and (sin or (silicon adj	USPAT;	2003/05/17 10:54
		nitride))	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
25	1	5479054.pn. and (sin or (silicon adj	USPAT;	2003/05/17 10:54
23	_	nitride))	US-PGPUB;	2000,00,1, 10.01
			EPO; JPO;	
			DERWENT;	
!			IBM_TDB	
26	59	((metal or (metal adj silicide)) adj gate)	USPAT;	2003/05/17 11:56
]		and (nonvolatile adj memory)	US-PGPUB;	
			EPO; JPO;	
[DERWENT;	
27	1.7	((motal or (motal add silicida)) add sata)	IBM_TDB USPAT;	2003/05/17 11:56
4 '	17	((metal or (metal adj silicide)) adj gate) and (nonvolatile adj memory) and tungsten	USPAT; US-PGPUB;	2003/03/17 11:36
		and (nonvoidelie dd) memory, and congiten	EPO; JPO;	
			DERWENT;	
			IBM TDB	
28	785	(peripheral adj circuit adj region) and	USPĀT;	2003/05/17 12:47
		257/\$.ccls.	US-PGPUB;	
	į		EPO; JPO;	
			DERWENT;	
	2.5		IBM_TDB	0003/05/13 10 10
29	256		USPAT;	2003/05/17 12:48
		257/\$.ccls.	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
L				<u></u>

30	76	(peripheral adj circuit adj region) and	USPAT;	2003/05/17 1	12:47
		(nonvolatile adj memory) and 257/\$.ccls.	US-PGPUB;		
			EPO; JPO;		l
			DERWENT;		
			IBM TDB		
31	7	(contact adj hole adj diameter) and	USPAT;	2003/05/17 1	L2:48
		(nonvolatile adj memory) and 257/\$.ccls.	US-PGPUB;		
			EPO; JPO;		
			DERWENT;		İ
			IBM TDB		i